

2SD2420, 2SD2420A

Silicon NPN triple diffusion planar type darlington

For power amplification

Complementary to 2SB1623, 2SB1623A

■ Features

- High forward current transfer ratio h_{FE}
- Dielectric breakdown voltage of the package: > 5 kV

■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	60 80	V
Collector-emitter voltage (Base open)	V_{CEO}	60 80	V
Emitter-base voltage (Collector open)	V_{EBO}	5	V
Collector current	I_C	4	A
Peak collector current	I_{CP}	8	A
Collector power dissipation	P_C	30 2.0	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

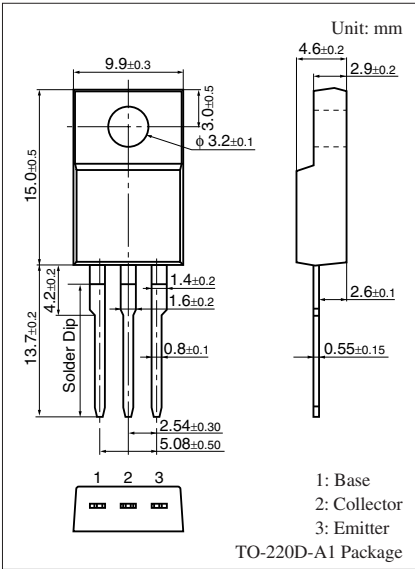
■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = 30 \text{ mA}, I_B = 0$	60			V
Base-emitter voltage	V_{BE}	$V_{CE} = 3 \text{ V}, I_C = 3 \text{ A}$			2.5	V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 60 \text{ V}, I_E = 0$ $V_{CB} = 80 \text{ V}, I_E = 0$			200 200	μA
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = 30 \text{ V}, I_B = 0$ $V_{CE} = 40 \text{ V}, I_B = 0$			500 500	μA
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = 5 \text{ V}, I_C = 0$			2	mA
Forward current transfer ratio	h_{FE1} h_{FE2}^*	$V_{CE} = 3 \text{ V}, I_C = 0.5 \text{ A}$ $V_{CE} = 3 \text{ V}, I_C = 3 \text{ A}$	1000 2000		10000	—
Collector-emitter saturation voltage	$V_{CE(sat)1}$ $V_{CE(sat)2}$	$I_C = 3 \text{ A}, I_B = 12 \text{ mA}$ $I_C = 5 \text{ A}, I_B = 20 \text{ mA}$			2.0 4.0	V
Transition frequency	f_T	$V_{CE} = 10 \text{ V}, I_C = 0.5 \text{ A}, f = 1 \text{ MHz}$		20		MHz
Turn-on time	t_{on}	$I_C = 3 \text{ A}, I_{B1} = 12 \text{ mA}, I_{B2} = -12 \text{ mA}$		0.5		μs
Storage time	t_{stg}	$V_{CC} = 50 \text{ V}$		4.0		μs
Fall time	t_f			1.0		μs

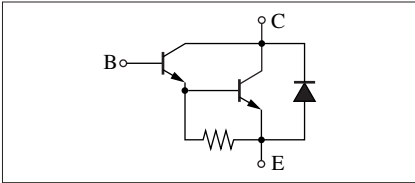
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

Rank	Q	P
h_{FE2}	2000 to 5000	4000 to 10000



Internal Connection



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